

L Number	Hits	Search Text	DB	Time stamp
-	7417	((438/149) or (438/164) or (438/180) or (438/181) or (438/182) or (438/479) or (438/482) or (438/488) or (438/514) or (438/574) or (438/673) or (438/701) or (438/713) or (438/738) or (438/745) or (438/948)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 14:50
-	430037	tft or (thin near2 film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 14:49
-	35286	(photoresist near2 pattern) or (photo near2 (mask or masks) )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/10 21:57
-	9434	(tft or (thin near2 film)) and ((photoresist near2 pattern) or (photo near2 (mask or masks) ))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:24
-	20524	reticle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:24
-	584	((tft or (thin near2 film)) and ((photoresist near2 pattern) or (photo near2 (mask or masks) ))) and reticle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:24
-	102	((((438/149) or (438/164) or (438/180) or (438/181) or (438/182) or (438/479) or (438/482) or (438/488) or (438/514) or (438/574) or (438/673) or (438/701) or (438/713) or (438/738) or (438/745) or (438/948)).CCLS.) and reticle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:24
-	14668	(ldd or (lightly near2 (doped adj drain)) near2 region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:26
-	8	((((438/149) or (438/164) or (438/180) or (438/181) or (438/182) or (438/479) or (438/482) or (438/488) or (438/514) or (438/574) or (438/673) or (438/701) or (438/713) or (438/738) or (438/745) or (438/948)).CCLS.) and reticle) and ((ldd or (lightly near2 (doped adj drain)) near2 region))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:27
-	639	((tft or (thin near2 film)) and ((photoresist near2 pattern) or (photo near2 (mask or masks) ))) and ((ldd or (lightly near2 (doped adj drain)) near2 region))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:27
-	81	((((438/149) or (438/164) or (438/180) or (438/181) or (438/182) or (438/479) or (438/482) or (438/488) or (438/514) or (438/574) or (438/673) or (438/701) or (438/713) or (438/738) or (438/745) or (438/948)).CCLS.) and (((tft or (thin near2 film)) and ((photoresist near2 pattern) or (photo near2 (mask or masks) ))) and ((ldd or (lightly near2 (doped adj drain)) near2 region)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:27
-	0	6548331.URPN.	USPAT	2004/01/09 21:37
-	11	("5403772"   "5488000"   "5569610"   "5581092"   "5821562"   "6066547"   "6097037"   "6133073"   "6221702"   "6278130"   "6300659").PN.	USPAT	2004/01/09 21:37
-	0	6440784.URPN.	USPAT	2004/01/09 21:38

	14	( "4514253"   "4654117"   "5627103"   "5686326"   "5714790"   "5733804" "5909615"   "5917199"   "5940151" "6166785"   "6204520"   "6232158" "6275275"   "6337234" ) . PN.	USPAT	2004/01/09 21:38
	14	( "4514253"   "4654117"   "5627103"   "5686326"   "5714790"   "5733804" "5909615"   "5917199"   "5940151" "6166785"   "6204520"   "6232158" "6275275"   "6337234" ) . PN.	USPAT	2004/01/09 21:40
	7	5668019.URPN.	USPAT	2004/01/09 21:41
	7	( "4479831"   "4577391"   "4629859"   "4727044"   "4751169"   "4980018"   "5214295" ) . PN.	USPAT	2004/01/09 21:43
	5054	t near2 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/09 21:44
	634	(t near2 gate) and (tft or (thin near2 film))	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/09 21:45
	87	((t near2 gate) and (tft or (thin near2 film))) and ((ldd or (lightly near2 (doped adj drain)) near2 region))	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/09 21:47
	0	(wider near (gate same (gate near2 dielectric))) and ((photoresist near2 pattern) or (photo near2 (mask or masks) ))	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/09 21:48
	2	wider near (gate same (gate near2 dielectric))	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/09 21:49
	0	((photoresist near2 pattern) or (photo near2 (mask or masks) )) near (gate same (gate near2 dielectric))	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/09 21:49
	15514	(gate same (gate near2 dielectric))	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/09 21:50
	168	((gate same (gate near2 dielectric))) same ((photoresist near2 pattern) or (photo near2 (mask or masks) ))	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/09 21:50
	48	((gate same (gate near2 dielectric))) same ((photoresist near2 pattern) or (photo near2 (mask or masks) )) and (tft or (thin near2 film))	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/09 21:52
	314	tapered near gate	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/09 21:53
	66	(tapered near gate) and (tft or (thin near2 film))	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/09 21:53

	35286	(photoresist near2 pattern) or (photo near2 (mask or masks) )	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/10 21:59
	837644	gate or (gate near2 electrode)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/11 15:25
	326	((photoresist near2 pattern) or (photo near2 (mask or masks) )) near (gate or (gate near2 electrode))	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/10 21:59
	430037	tft or (thin near2 film)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/10 21:59
	7417	((438/149) or (438/164) or (438/180) or (438/181) or (438/182) or (438/479) or (438/482) or (438/488) or (438/514) or (438/574) or (438/673) or (438/701) or (438/713) or (438/738) or (438/745) or (438/948)).CCLS.	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/10 22:00
	14	((((photoresist near2 pattern) or (photo near2 (mask or masks) )) near (gate or (gate near2 electrode))) and (tft or (thin near2 film))) and (((438/149) or (438/164) or (438/180) or (438/181) or (438/182) or (438/479) or (438/482) or (438/488) or (438/514) or (438/574) or (438/673) or (438/701) or (438/713) or (438/738) or (438/745) or (438/948)).CCLS.)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/10 22:00
	110	((photoresist near2 pattern) or (photo near2 (mask or masks) )) near (gate or (gate near2 electrode)) and (tft or (thin near2 film))	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/10 22:02
	0	6429485.URPN.	USPAT	2004/01/10 22:16
	0	("3890632"   "5292675"   "5323042"   "5757048"   "6031249").PN.	USPAT	2004/01/10 22:17
	430033	tft or (thin near2 film)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/11 15:22
	63417	color near2 filter	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/11 15:23
	7417	((438/149) or (438/164) or (438/180) or (438/181) or (438/182) or (438/479) or (438/482) or (438/488) or (438/514) or (438/574) or (438/673) or (438/701) or (438/713) or (438/738) or (438/745) or (438/948)).CCLS.	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/11 14:51
	12891	(tft or (thin near2 film)) and (color near2 filter)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/11 14:51
	6941	(tft or (thin near2 film)) same (color near2 filter)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/01/11 14:51

89	((tft or (thin near2 film)) same (color near2 filter)) and (((438/149) or (438/164) or (438/180) or (438/181) or (438/182) or (438/479) or (438/482) or (438/488) or (438/514) or (438/574) or (438/673) or (438/701) or (438/713) or (438/738) or (438/745) or (438/948)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 15:01
1176	pigment near substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 15:02
25	((tft or (thin near2 film)) same (pigment near substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 15:02
58114	tft or (thin near2 film near2 transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 15:22
1200433	(filter (color near2 filter))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 15:23
11039	((tft or (thin near2 film near2 transistor)) and ((filter (color near2 filter)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 15:24
1671185	pattern\$4 etch\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 15:24
7574	((tft or (thin near2 film near2 transistor)) and ((filter (color near2 filter))) and (pattern\$4 etch\$))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 15:24
837638	gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 15:25
4855	(((tft or (thin near2 film near2 transistor)) and ((filter (color near2 filter)))) and (pattern\$4 etch\$)) and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 15:26
556043	capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 15:26
2366	(((tft or (thin near2 film near2 transistor)) and ((filter (color near2 filter)))) and (pattern\$4 etch\$)) and gate ) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 15:27
443038	implant\$3 dop\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 15:27
1550	((((tft or (thin near2 film near2 transistor)) and ((filter (color near2 filter)))) and (pattern\$4 etch\$)) and gate ) and capacitor) and (implant\$3 dop\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 15:31

	88984	polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/11 15:32
	720	(((((tft or (thin near2 film near2 transistor)) and ((filter (color near2 filter)))) and (pattern\$4 etch\$)) and gate ) and capacitor) and (implant\$3 dop\$4)) and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/11 15:32